

L Number	Hits	Search Text	DB	Time stamp
-	13615	interconnect\$4 and metallization	USPAT	2002/07/23 15:57
-	12026	(interconnect\$4 and metallization) and (trench opening via hole groove)	USPAT	2002/07/23 15:57
-	11649	((interconnect\$4 and metallization) and (trench opening via hole groove)) and (metal adj3 (layer film) conducting conductive contact)	USPAT	2002/07/23 15:58
-	11649	((interconnect\$4 and metallization) and (trench opening via hole groove)) and ((metal adj3 (layer film)) conducting conductive contact)	USPAT	2002/07/23 15:57
-	16522	interconnect\$4 and metallization	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 15:57
-	13907	(interconnect\$4 and metallization) and (trench opening via hole groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 15:58
-	13267	((interconnect\$4 and metallization) and (trench opening via hole groove)) and (metal adj3 (layer film) conducting conductive contact)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 15:59
-	6482	((((interconnect\$4 and metallization) and (trench opening via hole groove)) and (metal adj3 (layer film) conducting conductive contact)) and ('FOX' 'LOCOS' isolat\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 16:01
-	872	(((((interconnect\$4 and metallization) and (trench opening via hole groove)) and (metal adj3 (layer film) conducting conductive contact)) and ('FOX' 'LOCOS' isolat\$3)) and (titanium adj3 (layer film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 16:02
-	834	((((((interconnect\$4 and metallization) and (trench opening via hole groove)) and (metal adj3 (layer film) conducting conductive contact)) and ('FOX' 'LOCOS' isolat\$3)) and (titanium adj3 (layer film)))) and (dielectric insulat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 16:03
-	389	((((((((interconnect\$4 and metallization) and (trench opening via hole groove)) and (metal adj3 (layer film) conducting conductive contact)) and ('FOX' 'LOCOS' isolat\$3)) and (titanium adj3 (layer film)))) and (dielectric insulat\$3)) and voltage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 16:03
-	389	(((((((((interconnect\$4 and metallization) and (trench opening via hole groove)) and (metal adj3 (layer film) conducting conductive contact)) and ('FOX' 'LOCOS' isolat\$3)) and (titanium adj3 (layer film)))) and (dielectric insulat\$3)) and voltage) and (first second)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 16:09
-	17	((((((((((interconnect\$4 and metallization) and (trench opening via hole groove)) and (metal adj3 (layer film) conducting conductive contact)) and ('FOX' 'LOCOS' isolat\$3)) and (titanium adj3 (layer film)))) and (dielectric insulat\$3)) and voltage) and (first second)) and metal adj trace	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 16:05
-	120	((((((((((interconnect\$4 and metallization) and (trench opening via hole groove)) and (metal adj3 (layer film) conducting conductive contact)) and ('FOX' 'LOCOS' isolat\$3)) and (titanium adj3 (layer film)))) and (dielectric insulat\$3)) and voltage) and (first second)) and plug	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 16:10
-	1		USPAT	2002/07/23 18:02
-	1		USPAT	2002/07/23 18:02

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(((interconnect\$4 and metallization) and (trench opening via hole groove)) and (metal adj3 (layer film) conducting conductive contact)) and ('FOX' LOCOS' isolat\$3)) and (titanium adj3 (layer film))) and (dielectric insulat\$3)) and voltage) and (first second)) and plug

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	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
100	<input type="checkbox"/>	<input type="checkbox"/>	US 5320975 A	19940614	19	Method of forming thin film pseudo-planar FET devices and struc	438/153	257/69; 257/903;
101	<input type="checkbox"/>	<input type="checkbox"/>	US 5182225 A	19930126	66	Process for fabricating BICMOS with hypershallow junctions	438/202	257/276; 257/370;
102	<input type="checkbox"/>	<input type="checkbox"/>	US 5171713 A	19921215	66	Process for forming planarized, air-bridge interconnects on a semicon	438/31	148/DIG.20; 257/750;
103	<input type="checkbox"/>	<input type="checkbox"/>	US 5134083 A	19920728	66	Method of forming self-aligned contacts in a semiconductor process	438/234	148/DIG.19; 438/233
104	<input type="checkbox"/>	<input type="checkbox"/>	US 5132237 A	19920721	66	Planarization method for fabricating high density semiconductor devices	438/294	438/1; 438/359
105	<input type="checkbox"/>	<input type="checkbox"/>	US 5117276 A	19920526	17	High performance interconnect system for an integrated circuit	257/758	216/15; 216/99;
106	<input type="checkbox"/>	<input type="checkbox"/>	US 5112761 A	19920512	68	BiCMOS process utilizing	438/207	257/370;